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April 2011

FDT434P

P-Channel 2.5V Specified PowerTrench® MOSFET

General Description

This P-Channel 2.5V specified MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

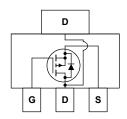
Applications

- Low Dropout Regulator
- DC/DC converter
- · Load switch
- Motor driving

Features

- -5.5 A, -20 V. $R_{DS(ON)}$ = 0.050 Ω @ V_{GS} = -4.5 V $R_{DS(ON)}$ = 0.070 Ω @ V_{GS} = -2.5 V.
- Low gate charge (13nC typical)
- High performance trench technology for extremely low $R_{\mbox{\scriptsize DS}(\mbox{\scriptsize ON})}$.
- High power and current handling capability in a widely used surface mount package.





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units	
V _{DSS}	Drain-Source Voltage		-20	V	
V _{GSS}	Gate-Source Voltage		±8	V	
I _D	Drain Current - Continuous	(Note 1a)	-6	Α	
	- Pulsed		-30		
P _D	Power Dissipation for Single Operation	(Note 1a)	3	W	
		(Note 1b)	1.3		
		(Note 1c)	1.1		
T _J , T _{stg}	Operating and Storage Junction Temperature Range		-55 to +150	°C	

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	42	°C/W
R _{eJC}	Thermal Resistance, Junction-to-Case	(Note 1)	12	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
434	FDT434P	13"	12mm	2500 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics			ı	I.	I.
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-20			V
<u>ΔBV_{DSS}</u> ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = -250 μ A,Referenced to 25°C		-28		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μΑ
I _{GSSF}	Gate–Body Leakage Current, Forward	V _{GS} = 8 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate–Body Leakage Current, Reverse	$V_{GS} = -8 \text{ V}$ $V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-0.4	-0.6	-1	V
$\Delta V_{GS(th)} = \Delta T_J$	Gate Threshold Voltage Temperature Coefficient	I_D = -250 μ A,Referenced to 25°C		2		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	V _{GS} = -4.5 V, I _D = -6 A V _{GS} = -2.5 V, I _D = -4 A V _{GS} = -4.5 V, I _D = -6 A T _J =125°C		0.040 0.050 0.067	0.050 0.070 0.083	Ω
I _{D(on)}	On–State Drain Current	$V_{GS} = -4.5 \text{ V}, I_D = -6 \text{ A T}_J = 125^{\circ}\text{C}$ $V_{GS} = -4.5 \text{ V}, V_{DS} = -5 \text{ V}$	-20			Α
g FS	Forward Transconductance	$V_{DS} = -10 \text{ V}, \qquad I_{D} = -6 \text{ A}$		6.5		S
Dvnamio	Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = -10 \text{ V}, \qquad V_{GS} = 0 \text{ V},$		1187		pF
Coss	Output Capacitance	f = 1.0 MHz		270		pF
C _{rss}	Reverse Transfer Capacitance	1		114		pF
Switchir	g Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = -5 \text{ V}, \qquad I_{D} = -1 \text{ A},$		8	16	ns
t _r	Turn-On Rise Time	$V_{GS} = -4.5 \text{ V}, R_{GEN} = 6 \Omega$		15	25	ns
t _{d(off)}	Turn-Off Delay Time	1		45	65	ns
t _f	Turn–Off Fall Time	7		30	50	ns
Q _g	Total Gate Charge	$V_{DS} = -10 \text{ V}, \qquad I_{D} = -6 \text{ A},$		13	19	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = -4.5 \text{ V}$		1.8		nC
Q_{gd}	Gate-Drain Charge			3		nC
Drain-S	ource Diode Characteristics	and Maximum Ratings				
Is	Maximum Continuous Drain-Source				-2.5	Α
V_{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = -2.5 \text{ A} \text{(Note 2)}$		-0.75	-1.2	V

Notes

^{1.} $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 42°C/W when mounted on a 1in² pad of 2 oz copper



b) 95°/W when mounted on a .0066 in² pad of 2 oz copper

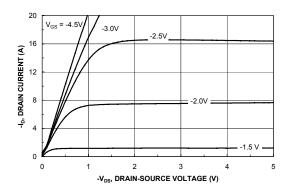


c) 110°/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300μ s, Duty Cycle < 2.0%

Typical Characteristics



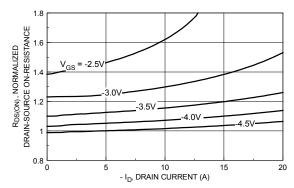
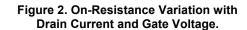
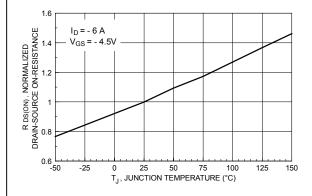


Figure 1. On-Region Characteristics.





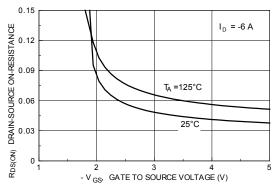
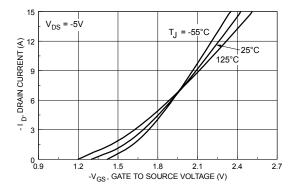


Figure 3. On-Resistance Variation withTemperature.

Figure 4. On-Resistance Variation with Gate-to-Source Voltage.



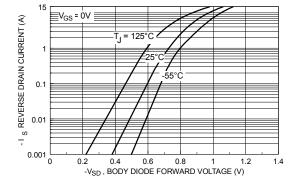


Figure 5. Transfer Characteristics.

Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

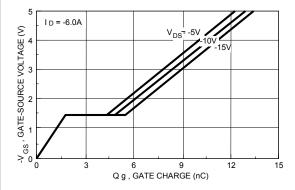
100

SINGLE PULSE

R_{eJA}= 110°C/W T_A= 25 °C

1D, DRAIN CURRENT (A)

0.01



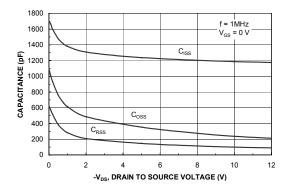


Figure 7. Gate Charge Characteristics.

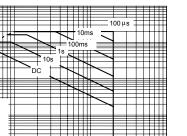


Figure 8. Capacitance Characteristics.

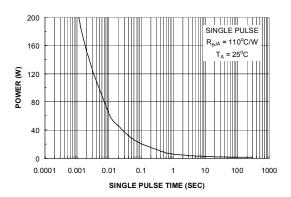


Figure 9. Maximum Safe Operating Area.

-V DS DRAIN-SOURCE VOLTAGE (V)



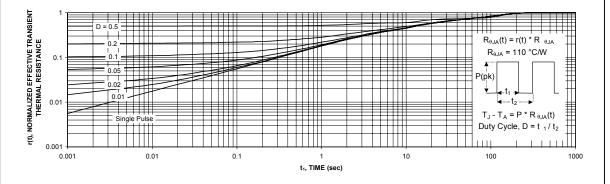
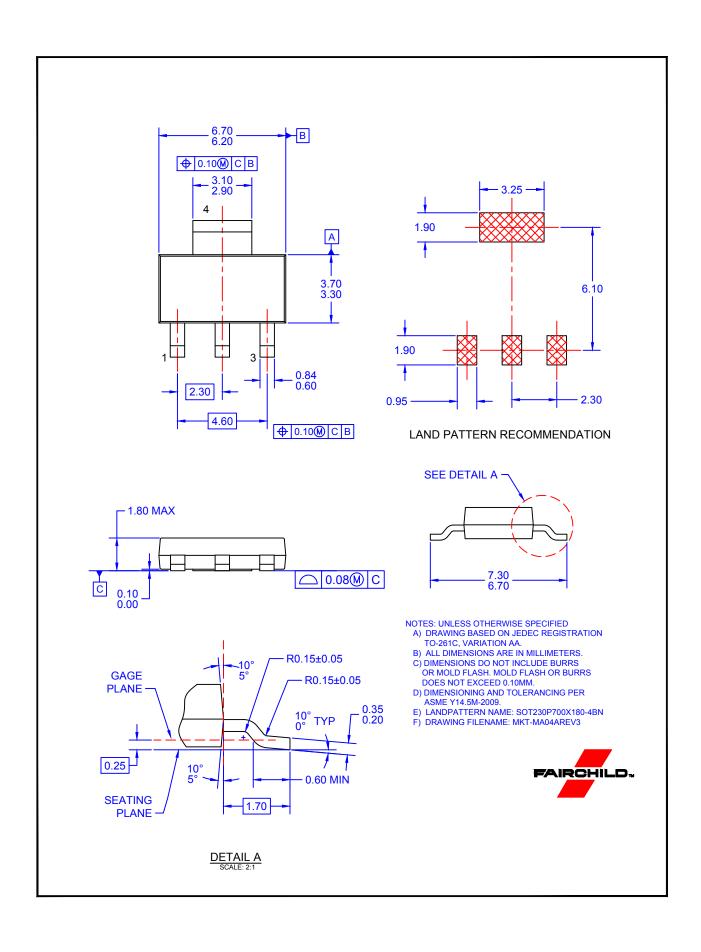


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.



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